



SEMITRANS® 3

IGBT4 Modules

SKM200GAL12E4

Features

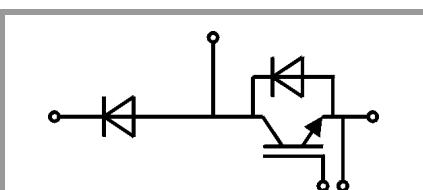
- IGBT4 = 4. generation medium fast trench IGBT (Infineon)
- CAL4 = Soft switching 4. generation CAL-diode
- Isolated copper baseplate using DBC technology (Direct Bonded Copper)
- Increased power cycling capability
- With integrated gate resistor
- For higher switching frequencies up to 12kHz
- UL recognized, file no. E63532

Typical Applications*

- DC/DC – converter
- Brake chopper
- Switched reluctance motor

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max.
- Recommended $T_{op} = -40 \dots +150^\circ\text{C}$
- Product reliability results valid for $T_j = 150^\circ\text{C}$



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Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	T _j = 175 °C	T _c = 25 °C	313	A
		T _c = 80 °C	241	A
I _{Cnom}			200	A
I _{CRM}	I _{CRM} = 3xI _{Cnom}		600	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 150 °C	10	μs
T _j			-40 ... 175	°C

Inverse diode

I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	229	A
		$T_c = 80^\circ\text{C}$	172	A
I_{Fnom}			200	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		600	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$		990	A
T_j			-40 ... 175	$^\circ\text{C}$

Freewheeling diode

I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	229	A
		$T_c = 80^\circ\text{C}$	172	A
I_{Fnom}			200	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		600	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$		990	A
T_j			-40 ... 175	$^\circ\text{C}$

Module

$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$	500	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50 Hz, $t = 1\text{ min}$	4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 200\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.80	2.05	V
		$T_j = 150^\circ\text{C}$	2.20	2.40	V
V_{CE0}	chipelevel	$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	5.00	5.75	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	7.50	8.00	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 7.6\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$		2.7	mA
		$T_j = 150^\circ\text{C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	12.3		nF
C_{oes}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	0.81		nF
C_{res}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	0.69		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		1130		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		3.8		Ω



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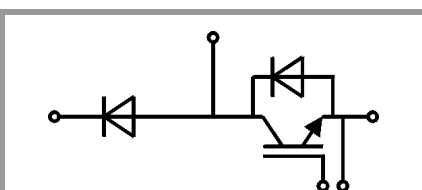
Typical Applications*

- DC/DC – converter
- Brake chopper
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Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max.
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- Product reliability results valid for $T_j = 150^\circ\text{C}$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
t _{d(on)}	V _{CC} = 600 V	T _j = 150 °C		204		ns
t _r	I _C = 200 A	T _j = 150 °C		40		ns
E _{on}	V _{GE} = ±15 V	T _j = 150 °C		21		mJ
t _{d(off)}	R _{G on} = 1 Ω	T _j = 150 °C		490		ns
t _f	di/dt _{on} = 5500 A/μs	T _j = 150 °C		107		ns
E _{off}	di/dt _{off} = 2300 A/μs	T _j = 150 °C		27		mJ
R _{th(j-c)}	per IGBT				0.14	K/W
Inverse diode						
V _F = V _{EC}	I _F = 200 A	T _j = 25 °C		2.20	2.52	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.15	2.47	V
V _{F0}	chiplevel	T _j = 25 °C		1.3	1.5	V
		T _j = 150 °C		0.9	1.1	V
r _F	chiplevel	T _j = 25 °C		4.5	5.1	mΩ
		T _j = 150 °C		6.3	6.8	mΩ
I _{RRM}	I _F = 200 A	T _j = 150 °C		174		A
Q _{rr}	di/dt _{off} = 4450 A/μs	T _j = 150 °C		33		μC
E _{rr}	V _{GE} = ±15 V	T _j = 150 °C		13		mJ
	V _{CC} = 600 V					
R _{th(j-c)}	per diode				0.26	K/W
Freewheeling diode						
V _F = V _{EC}	I _F = 200 A	T _j = 25 °C		2.20	2.52	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.15	2.47	V
V _{F0}	chiplevel	T _j = 25 °C		1.3	1.5	V
		T _j = 150 °C		0.9	1.1	V
r _F	chiplevel	T _j = 25 °C		4.5	5.1	mΩ
		T _j = 150 °C		6.3	6.8	mΩ
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Q _{rr}	di/dt _{off} = 4450 A/μs	T _j = 150 °C		33.1		μC
E _{rr}	V _{GE} = ±15 V	T _j = 150 °C		13		mJ
	V _{CC} = 600 V					
R _{th(j-c)}	per Diode				0.26	K/W
Module						
L _{CE}				15	20	nH
R _{CC'+EE'}	terminal-chip	T _C = 25 °C		0.25		mΩ
		T _C = 125 °C		0.5		mΩ
R _{th(c-s)}	per module			0.02	0.038	K/W
M _s	to heat sink M6		3		5	Nm
M _t		to terminals M6	2.5		5	Nm
						Nm
w					325	g



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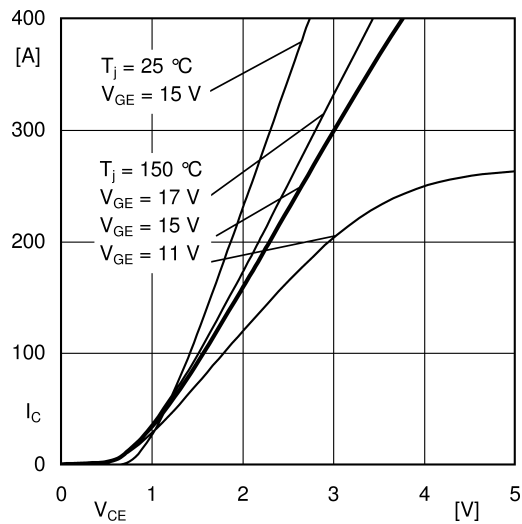


Fig. 1: Typ. output characteristic, inclusive $R_{CC'} + E_E$

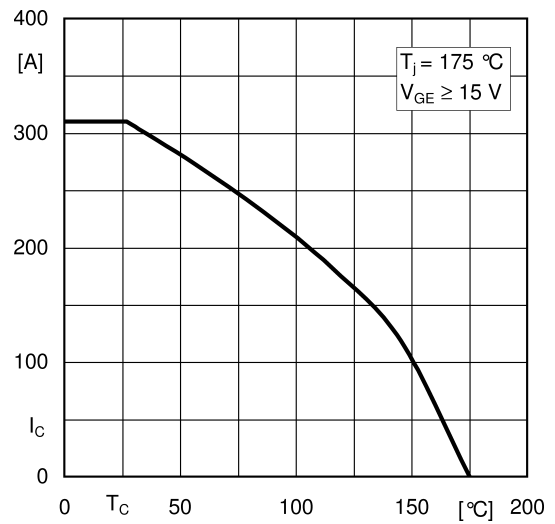


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

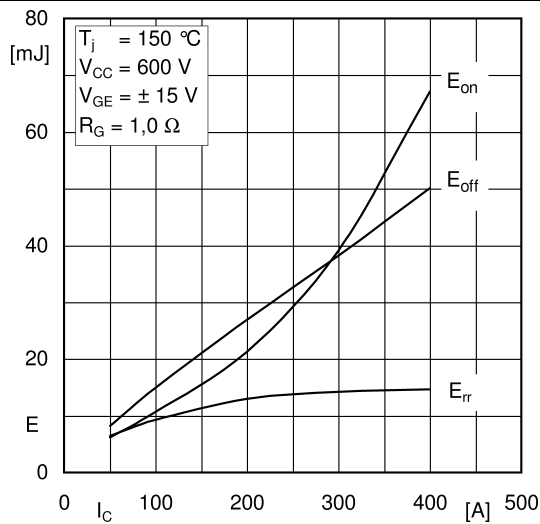


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

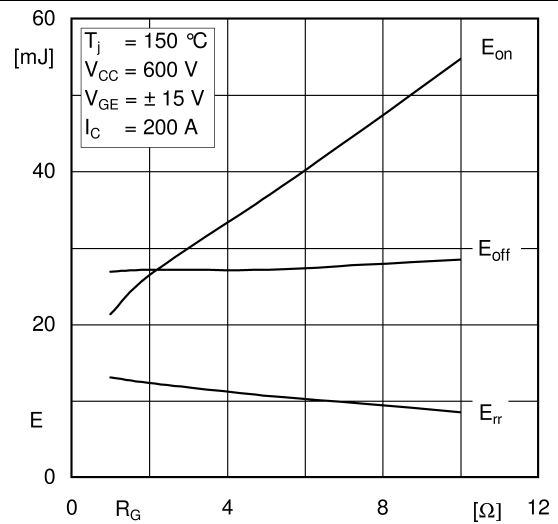


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

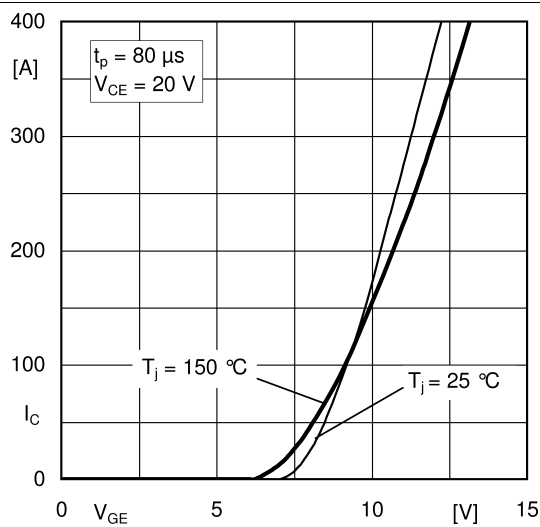


Fig. 5: Typ. transfer characteristic

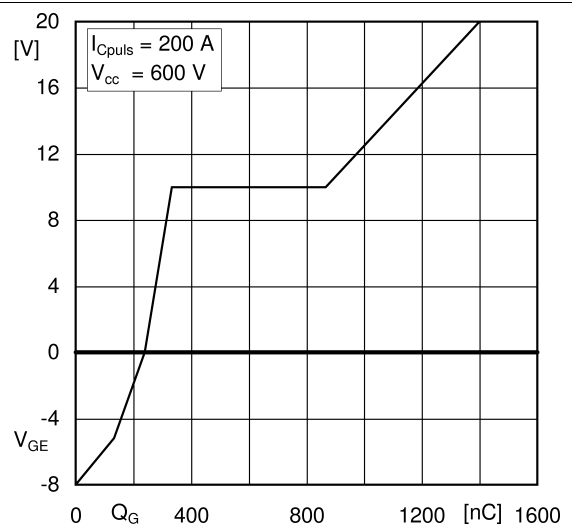
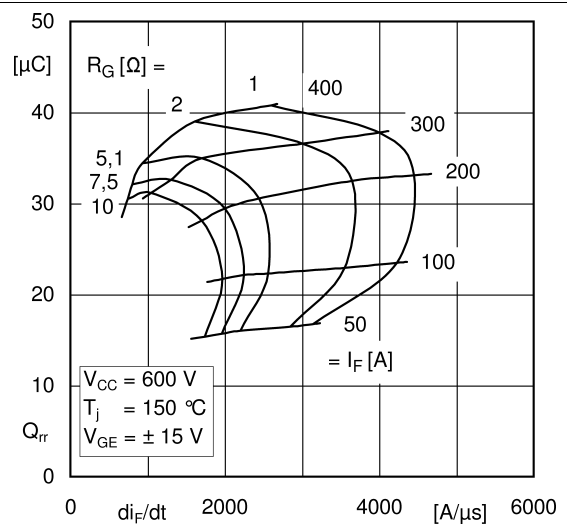
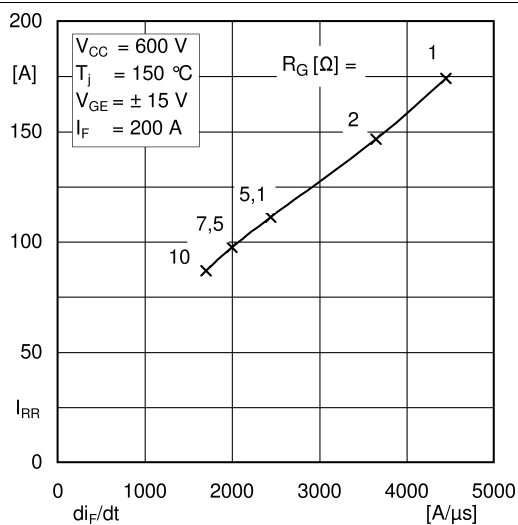
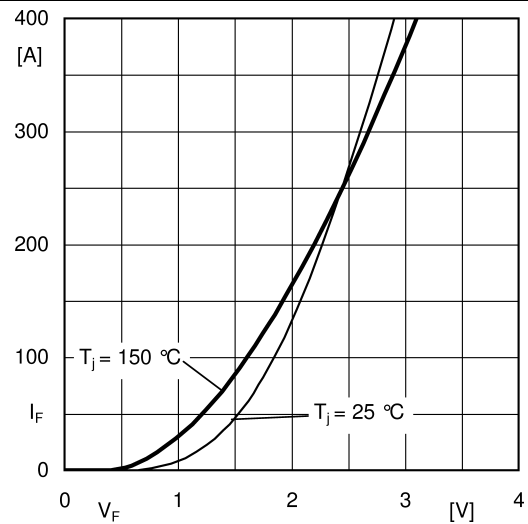
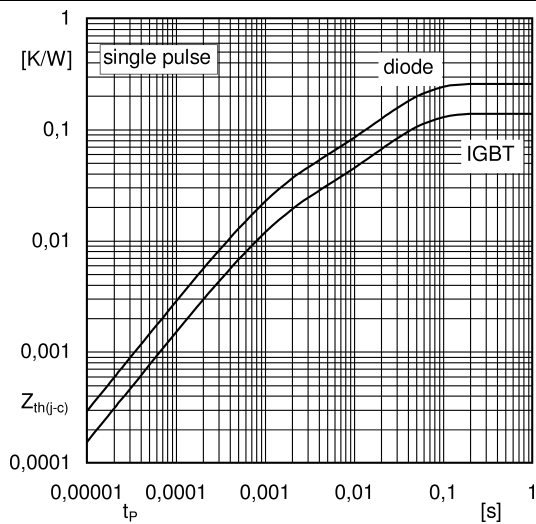
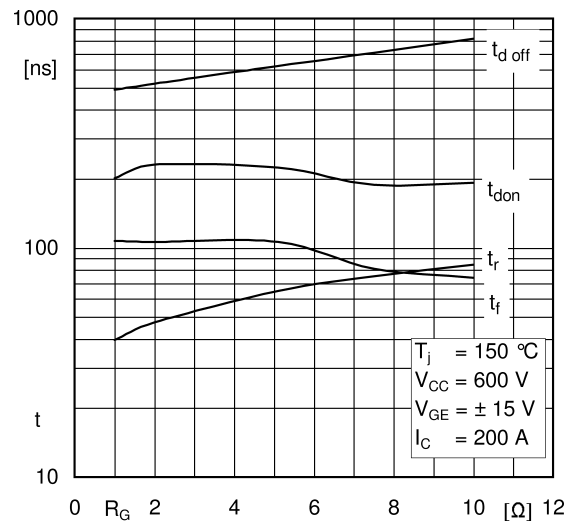
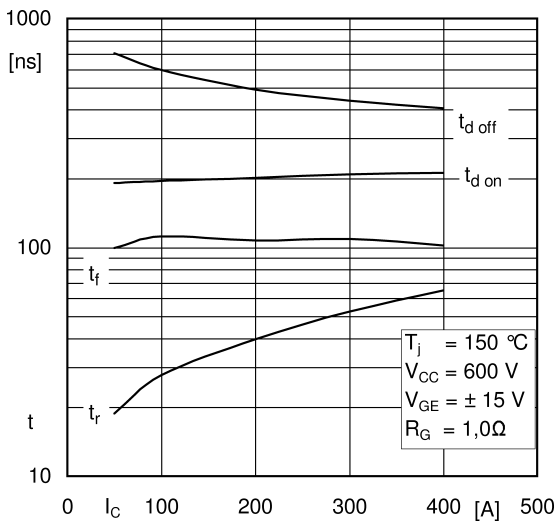
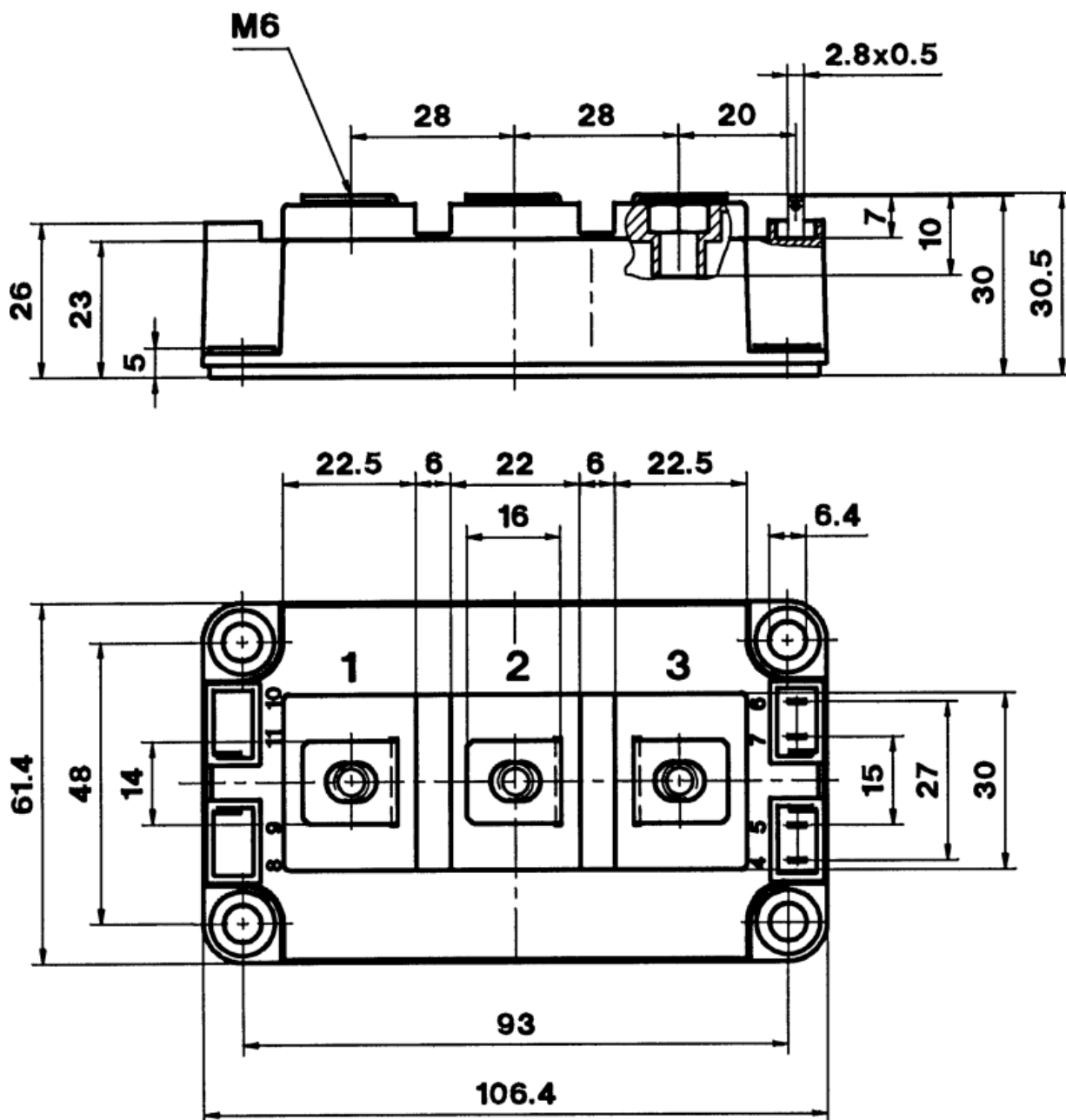
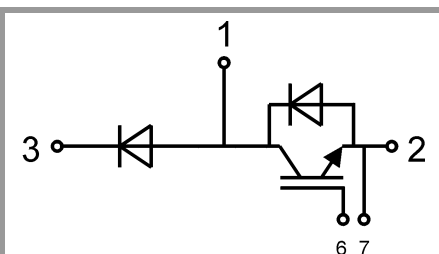


Fig. 6: Typ. gate charge characteristic





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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.